



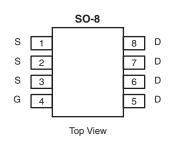
# N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)			
20	0.025 at V <sub>GS</sub> = 4.5 V	± 8.5			
	0.035 at V <sub>GS</sub> = 2.5 V	± 7.1			

### **FEATURES**

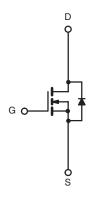
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4426DY-T1-E3 (Lead (Pb)-free)

Si4426DY-T1-GE3 (Lead (Pb)-free and Halogen free)



N-Channel MOSFET

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	20		V
Gate-Source Voltage		$V_{GS}$	± 12		
Continuous Drain Current /T 150 °C\a	T <sub>A</sub> = 25 °C	I <sub>D</sub>	± 8.5	± 6.5	А
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		± 6.8	± 5.2	
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	± 40		A	
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	2.1	2.1		
Maniana Davias Disainational	T <sub>A</sub> = 25 °C	P <sub>D</sub> 2.5 1.5 1.6 0.9	1.5	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		1.6	0.9	VV
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55	to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	R <sub>thJA</sub>	38	50	°C/W
Maximum Sunction-to-Ambient	Steady State		70	85	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	20	25	

Notes

a. Surface Mounted on 1" x 1" FR4 board.

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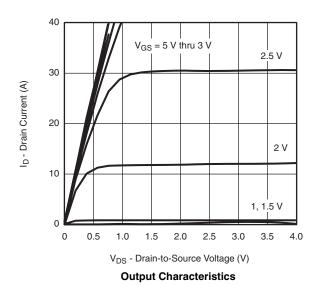
SPECIFICATIONS $T_J = 25$ °	C, unless	otherwise noted					
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6		1.4	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zoro Cata Valtaga Drain Current	lass	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	μΑ	
On-State Drain Current <sup>a</sup>	rent <sup>a</sup> $I_{D(on)}$ $V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$		40			Α	
	D	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 8.5 A		0.019	0.025	0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 7.1 \text{ A}$		0.025	0.035	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_{D} = 8.5 \text{ A}$		27		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 2.1 A, V <sub>GS</sub> = 0 V		0.8	1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg			25	50		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 8.5 \text{ A}$		6.5		nC	
Gate-Drain Charge	$Q_{gd}$			4		1	
Turn-On Delay Time	t <sub>d(on)</sub>			40	60		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$		40	60		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 $\Omega$		90	150	ns	
Fall Time	t <sub>f</sub>			40	60		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.1 A, dI/dt = 100 A/μs		40	60		

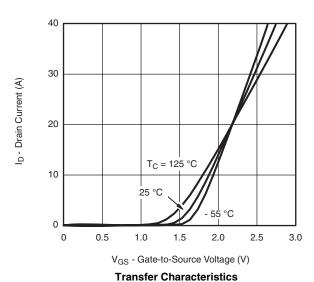
### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

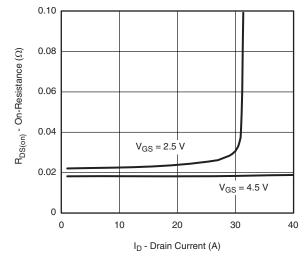




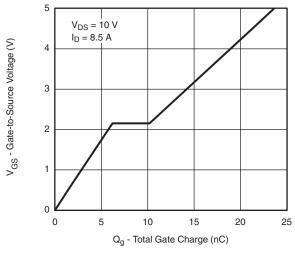




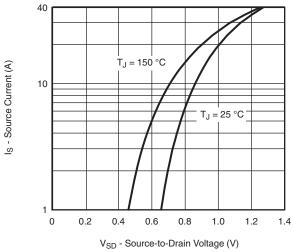
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



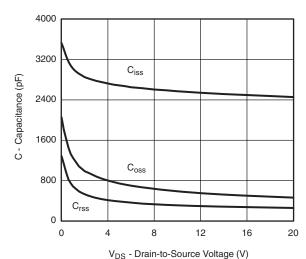
### On-Resistance vs. Drain Current



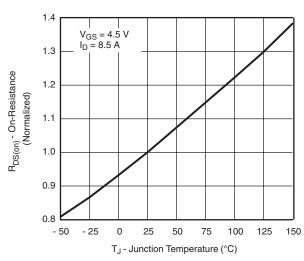
**Gate Charge** 



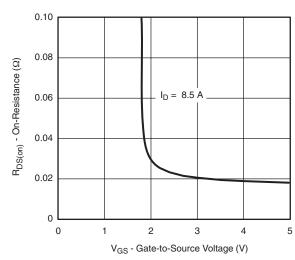
Source-Drain Diode Forward Voltage



Capacitance



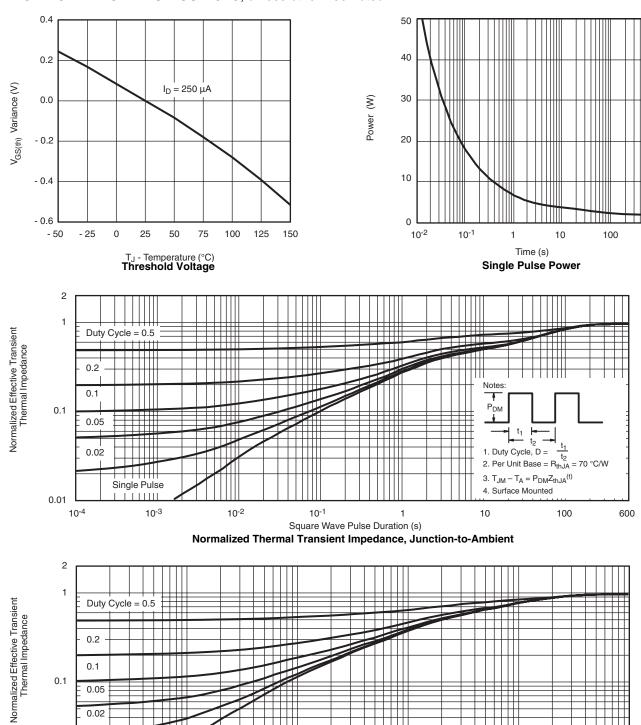
On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



### Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Foot

10-1

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71107.

0.02

0.01 10-4

Single Pulse

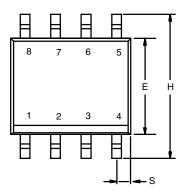
10-3

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIMETERS INCHES			HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27 BSC		0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
FCN: C-06527-Bey   11-Sen-06						

DWG: 5498

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### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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